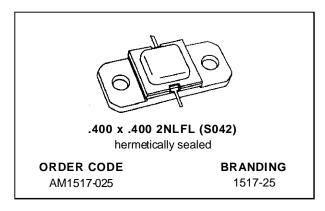


AM1517-025

RF & MICROWAVE TRANSISTORS SATELLITE COMMUNICATIONS APPLICATIONS

- REFRACTORY/GOLD METALLIZATION
- EMITTER SITE BALLASTED
- ∞:1 VSWR CAPABILITY
- LOW THERMAL RESISTANCE
- INPUT/OUTPUT MATCHING
- OVERLAY GEOMETRY
- METAL/CERAMIC HERMETIC PACKAGE
- P_{OUT} = 25 W MIN. WITH 8.5 dB GAIN

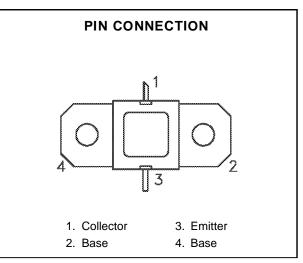


DESCRIPTION

The AM1517-025 power transistor is designed specifically for Satellite communications applications in the 1.5 – 1.7 GHz frequency range.

The device is capable of withstanding any mismatch load condition at any phase angle (VSWR ∞:1) under full rated conditions. The unit is an overlay, emitter site ballasted, geometry utilizing a Refactory/Gold metallization system.

The AM1517-025 is supplied in the AMPAC™ Hermetic/Ceramic package with internal Input/Output matching structures.



ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit	
P _{DISS}	Power Dissipation* (T _C ≤ 100°C)	45	W	
Ic	Device Current*	2.5	А	
Vcc	Collector-Supply Voltage*	30	V	
TJ	Junction Temperature	200	°C	
T _{STG}	Storage Temperature	- 65 to +200	°C	

THERMAL DATA

R _{TH(j-c)} Junction-Case Thermal Resistance*	3.3	°C/W
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^{*}Applies only to rated RF amplifier operation

September 1992

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

Symbol	Test Conditions	Value			Unit
		Min.	Тур.	Max.	Unit
BV _{CBO}	$I_C = 8mA$ $I_E = 0mA$	45	_	_	V
BVEBO	$I_E = 8mA$ $I_C = 0mA$	3.0	_	_	V
Ісво	V _{CB} = 28V	_	_	2	mA
h _{FE}	$V_{CE} = 5V$ $I_{C} = 1.6A$	15	_	150	_

DYNAMIC

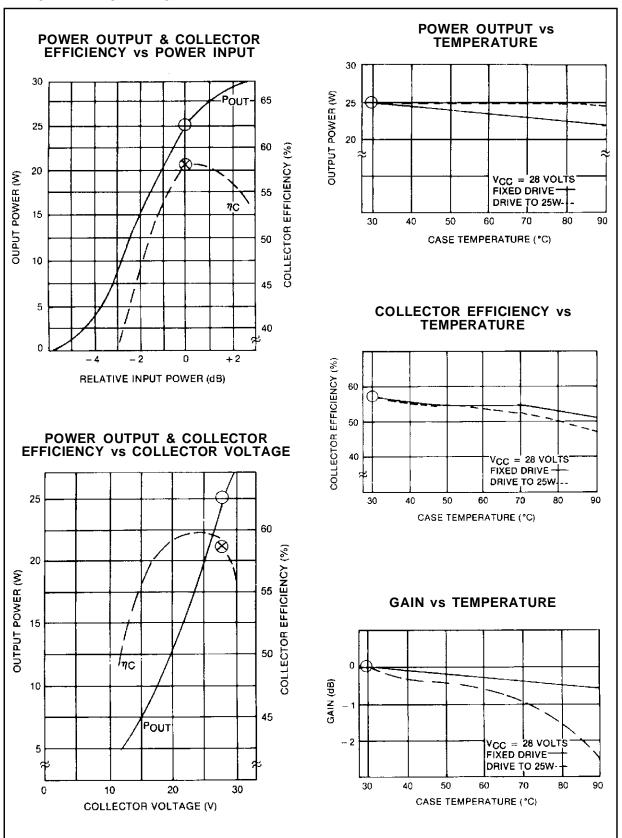
Symbol	Test Conditions		Value		Unit		
Symbol		rest Conditions			Тур.	Max.	Unit
Pout	f = 1.5 — 1.7GHz	$P_{IN} = 3.5W$	$V_{CC} = 28V$	25	_	_	W
ης	f = 1.5 — 1.7GHz	$P_{IN} = 3.5W$	$V_{CC} = 28V$	55	58	_	%
G _P	f = 1.5 — 1.7GHz	$P_{IN} = 3.5W$	$V_{CC} = 28V$	8.5	_	_	dB

Note: AM1517 series vary P_{IN} to achieve P_{OUT}; performance guaranteed in 50 MHz increments.

Alpha-Suffix added to AM1517 P/N designates band segment.

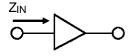
A -1500 - 1550 MHz M -1620 - 1660 MHz S -1625 - 1675 MHz

TYPICAL PERFORMANCE

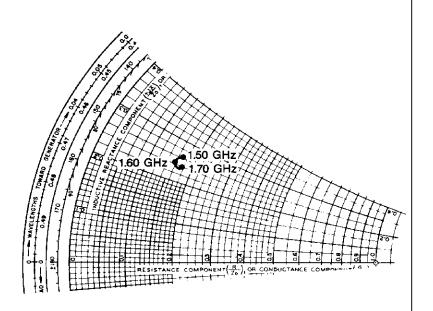


IMPEDANCE DATA



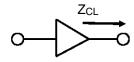


 $\begin{aligned} P_{OUT} &= 25 \text{ W} \\ V_{CC} &= 28 \text{ V} \\ Z_{O} &= 50 \text{ ohms} \end{aligned}$

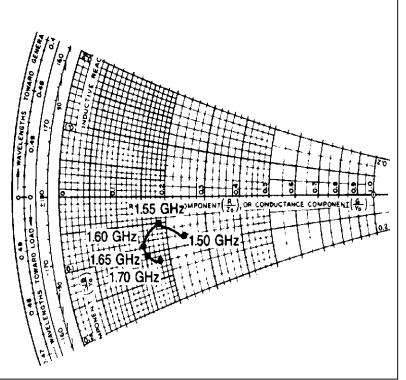


FREQ.	Z _{IN} (Ω)	Z _{CL} (Ω)		
L = 1.5 GHz	8.5 + j 13.0	12.0 – j 4.0		
M = 1.6 GHz	8.0 + j 12.5	7.5 – j 4.5		
H = 1.7 GHz	9.0 + j 12.0	9.0 – j 6.0		

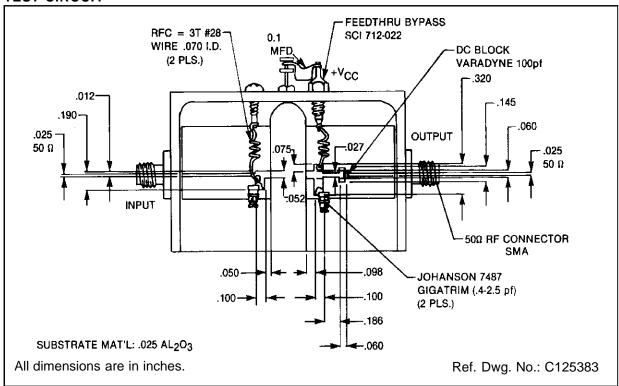
TYPICAL COLLECTOR LOAD IMPEDANCE



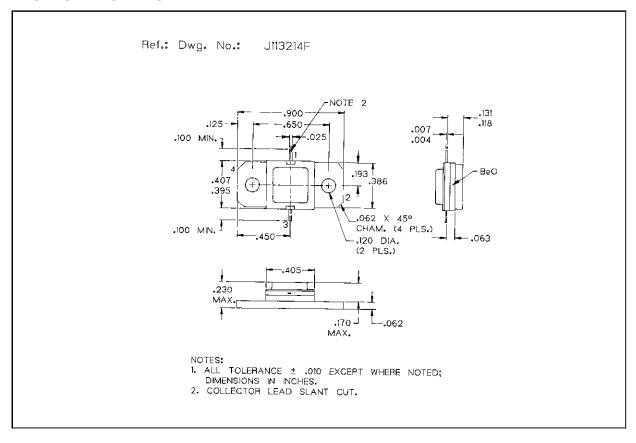
 $P_{OUT} = 25 \text{ W}$ $V_{CC} = 28 \text{ V}$ $Z_{O} = 50 \text{ ohms}$



TEST CIRCUIT



PACKAGE MECHANICAL DATA



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